

MOSFET – P-Channel, POWERTRENCH®

-150 V, -1 A, 1.2 Ω

FDMA86265P

General Description

This P-Channel MOSFET is produced using **onsemi**'s advanced POWERTRENCH process that has been optimized for the on-state resistance and yet maintain superior switching performance.

Features

- Max $r_{DS(on)}$ = 1.2 mΩ at $V_{GS} = -10$ V, $I_D = -1$ A
- Max $r_{DS(on)}$ = 1.4 mΩ at $V_{GS} = -6$ V, $I_D = -0.9$ A
- Low Profile – 0.8 mm Maximum in the New Package MicroFET™ 2x2 mm
- Very Low RDS-on Mid Voltage P-channel Silicon Technology Optimised for Low Qg
- This Product is Optimised for Fast Switching Applications as Well as Load Switch Applications
- 100% UIL Tested
- This Device is Pb-Free, Halide Free and is RoHS Compliant

Applications

- Active Clamp Switch
- Load Switch

MOSFET MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

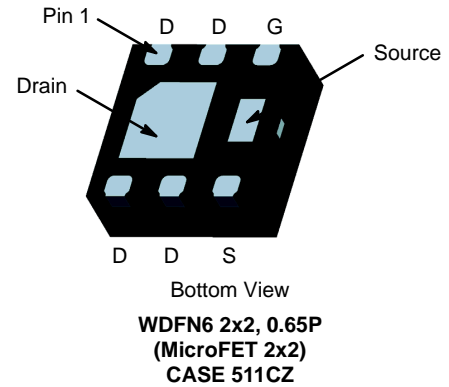
Symbol	Parameter	Ratings	Unit
V_{DS}	Drain to Source Voltage	-150	V
V_{GS}	Gate to Source Voltage	±25	V
I_D	Drain Current – Continuous $T_A = 25^\circ\text{C}$ (Note 1a) – Pulsed	-1 -2	A
E_{AS}	Single Pulse Avalanche Energy (Note 3)	6	mJ
P_D	Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1a) $T_A = 25^\circ\text{C}$ (Note 1b)	2.4 0.9	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

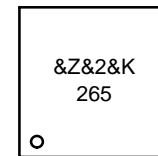
THERMAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Ratings	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	52	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1b)	145	

V_{DS}	$r_{DS(on)}$ MAX	I_D MAX
-150 V	1.2 mΩ @ -10 V	-1 A
	1.4 mΩ @ -6 V	

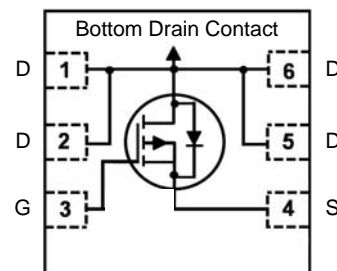


MARKING DIAGRAM



&Z = Assembly Plant Code
&2 = 2-Digit Date Code
&K = 2-Digits Lot Run Traceability Code
265 = Specific Device Code

PIN ASSIGNMENT



ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

FDMA86265P

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
--------	-----------	----------------	-----	-----	-----	------

OFF CHARACTERISTICS

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = -250 \mu\text{A}$, $V_{GS} = 0 \text{ V}$	-150	-	-	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250 \mu\text{A}$, referenced to 25°C	-	-125	-	mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -120 \text{ V}$, $V_{GS} = 0 \text{ V}$	-	-	-1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 25 \text{ V}$, $V_{DS} = 0 \text{ V}$	-	-	± 100	nA

ON CHARACTERISTICS

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = -250 \mu\text{A}$	-2	-3.2	-4	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = -250 \mu\text{A}$, referenced to 25°C	-	5	-	mV/ $^\circ\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = -10 \text{ V}$, $I_D = -1 \text{ A}$	-	0.86	1.2	Ω
		$V_{GS} = -6 \text{ V}$, $I_D = -0.9 \text{ A}$	-	0.95	1.4	
		$V_{GS} = -10 \text{ V}$, $I_D = -1 \text{ A}$, $T_J = 125^\circ\text{C}$	-	1.53	2.2	
g_{FS}	Forward Transconductance	$V_{DS} = -10 \text{ V}$, $I_D = -1 \text{ A}$	-	1.9	-	S

DYNAMIC CHARACTERISTICS

C_{iss}	Input Capacitance	$V_{DS} = -75 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$	-	158	210	pF
C_{oss}	Output Capacitance		-	16	25	pF
C_{rss}	Reverse Transfer Capacitance		-	0.7	5	pF
R_g	Gate Resistance		0.1	3	7.5	Ω

SWITCHING CHARACTERISTICS

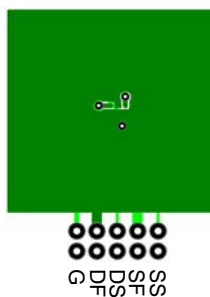
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -75 \text{ V}$, $I_D = -1 \text{ A}$, $V_{GS} = -10 \text{ V}$, $R_{GEN} = 6 \Omega$	-	5.8	12	ns
t_r	Rise Time		-	2.2	10	ns
$t_{d(off)}$	Turn-Off Delay Time		-	8	16	ns
t_f	Fall Time		-	6.4	13	ns
$Q_{g(TOT)}$	Total Gate Charge	$V_{GS} = 0 \text{ V}$ to -10 V , $V_{DD} = -75 \text{ V}$, $I_D = -1 \text{ A}$	-	2.8	4	nC
Q_{gs}	Total Gate Charge	$V_{DD} = -75 \text{ V}$, $I_D = -1 \text{ A}$	-	0.8	-	nC
Q_{gd}	Gate to Drain "Miller" Charge		-	0.7	-	nC

DRAIN-SOURCE CHARACTERISTICS

V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0 \text{ V}$, $I_S = -1 \text{ A}$ (Note 2)	-	-0.87	-1.3	V
t_{rr}	Reverse Recovery Time	$I_F = -1 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$	-	50	80	ns
Q_{rr}	Reverse Recovery Charge		-	78	124	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- $R_{\theta JA}$ is determined with the device mounted on a 1 in^2 pad 2 oz copper pad on a $1.5 \times 1.5 \text{ in.}$ board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. $52^\circ\text{C}/\text{W}$ when mounted on a 1 in^2 pad of 2 oz copper



b. $145^\circ\text{C}/\text{W}$ when mounted on a minimum pad of 2 oz copper

- Pulse Test: Pulse Width $< 300 \mu\text{s}$, Duty cycle $< 2.0\%$.
- Starting $T_J = 25^\circ\text{C}$; P-ch: $L = 3 \text{ mH}$, $I_{AS} = -2 \text{ A}$, $V_{DD} = -150 \text{ V}$, $V_{GS} = -10 \text{ V}$.

TYPICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, unless otherwise noted)

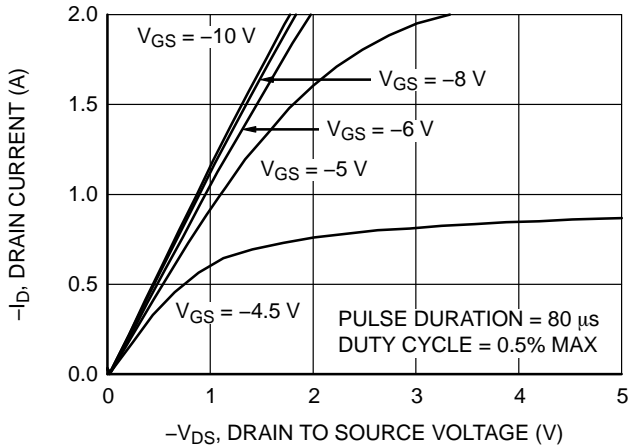


Figure 1. On Region Characteristics

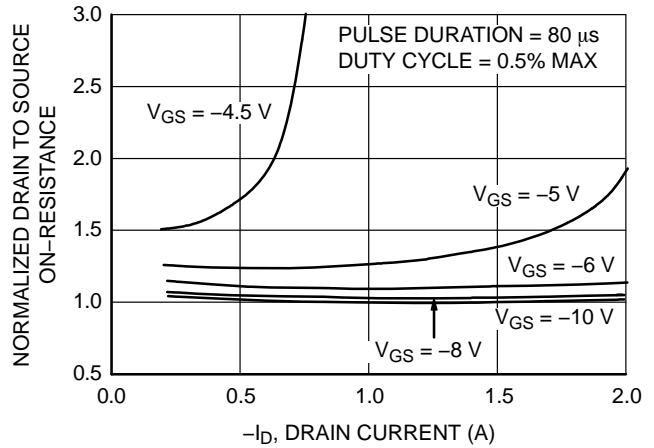


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

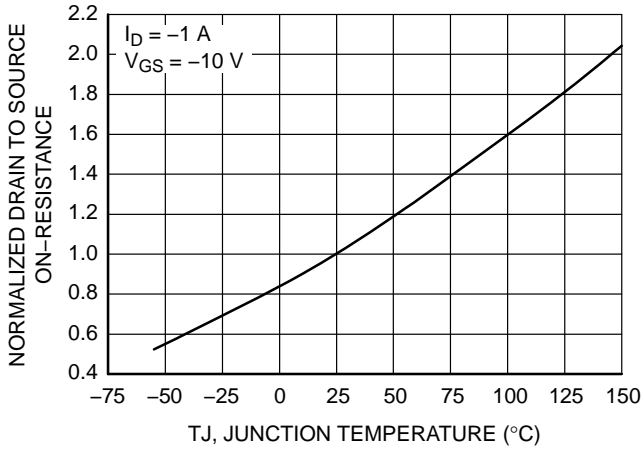


Figure 3. Normalized On Resistance vs. Junction Temperature

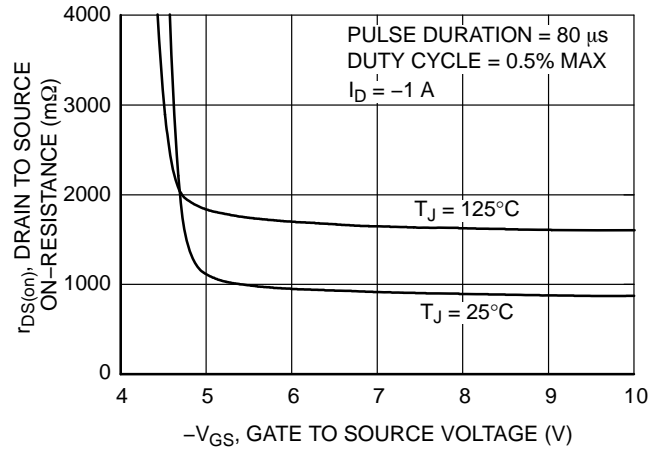


Figure 4. On-Resistance vs. Gate to Source Voltage

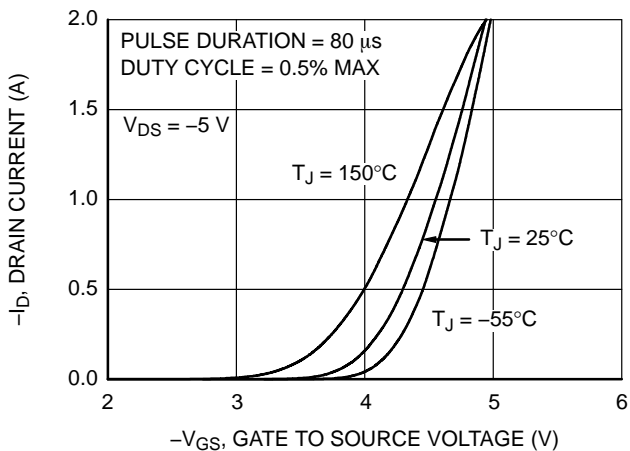


Figure 5. Transfer Characteristics

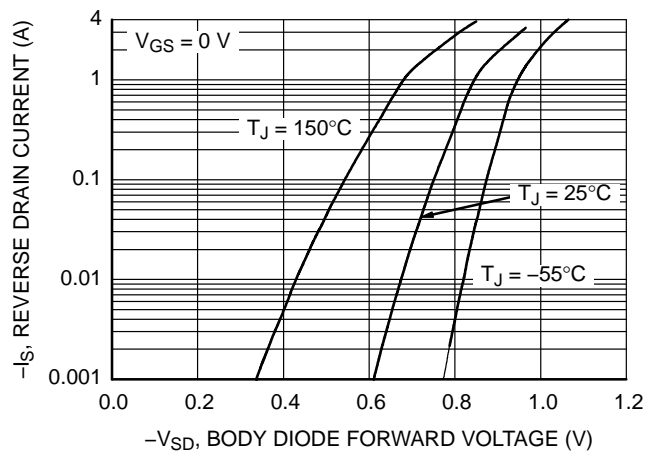


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

TYPICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, unless otherwise noted) (continued)

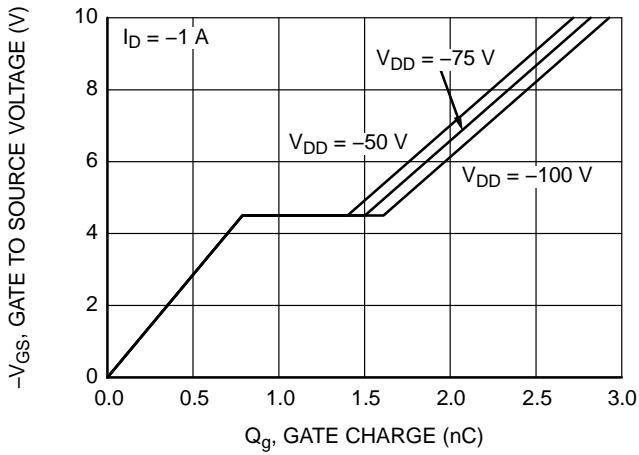


Figure 7. Gate Charge Characteristics

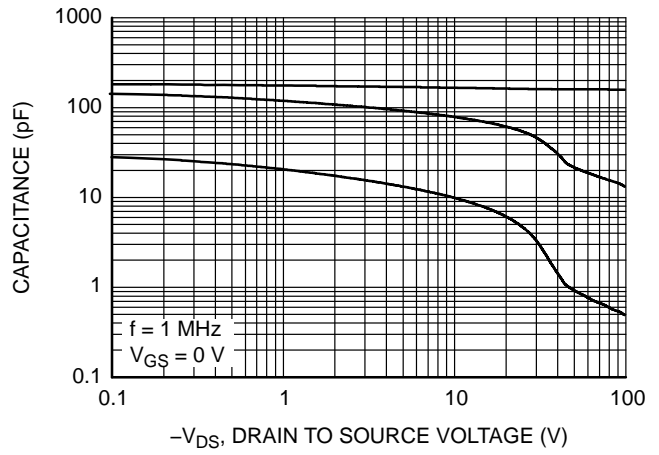


Figure 8. Capacitance vs. Drain to Source Voltage

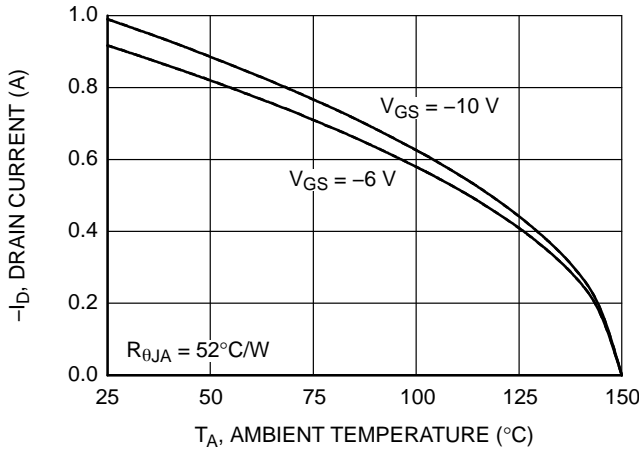


Figure 9. Maximum Continuous Drain Current vs. Ambient Temperature

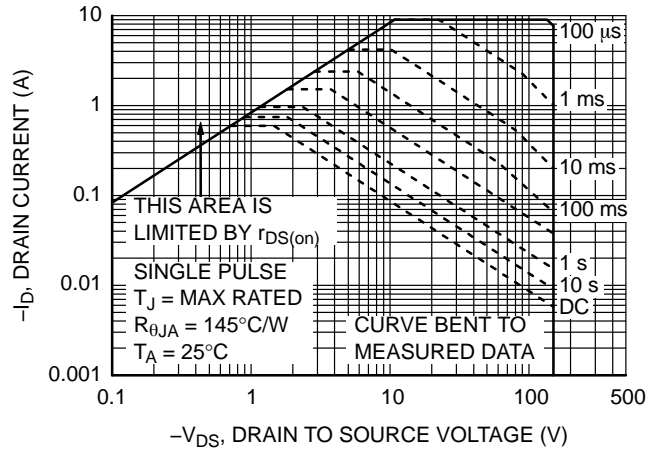


Figure 10. Forward Bias Safe Operating Area

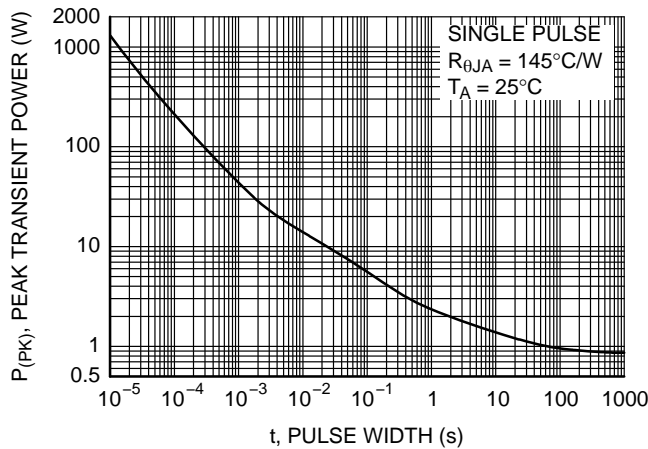


Figure 11. Single Pulse Maximum Power Dissipation

FDMA86265P

TYPICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, unless otherwise noted) (continued)

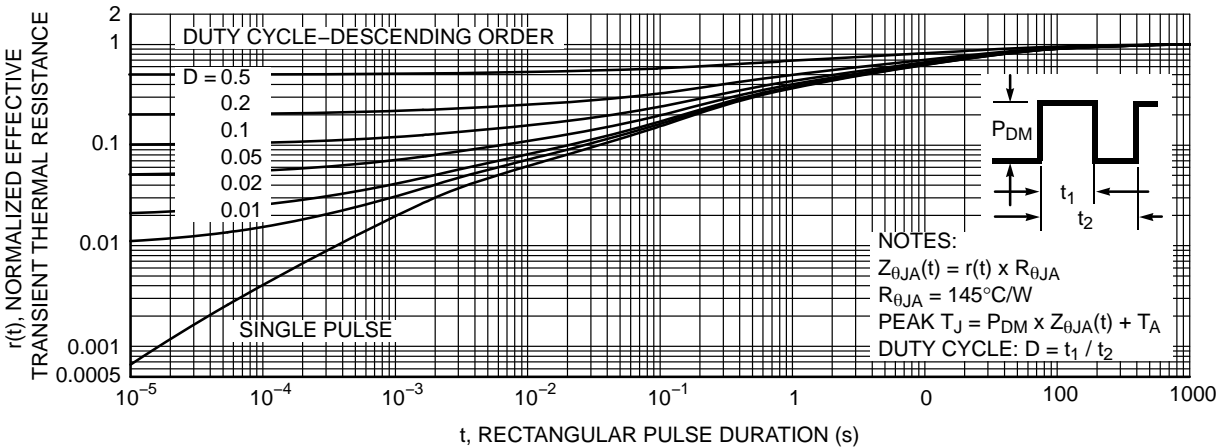


Figure 12. Junction-to-Ambient Transient Thermal Response Curve

PACKAGE MARKING AND ORDERING INFORMATION

Device	Device Marking	Package	Reel Size	Tape Width	Shipping†
FDMA86265P	265	WDFN6 2x2, 0.65P (MicroFET 2x2) (Pb-Free, Halide Free)	7"	12 mm	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

POWERTRENCH is registered trademark of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries.

MicroFET is trademark of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries.

MECHANICAL CASE OUTLINE

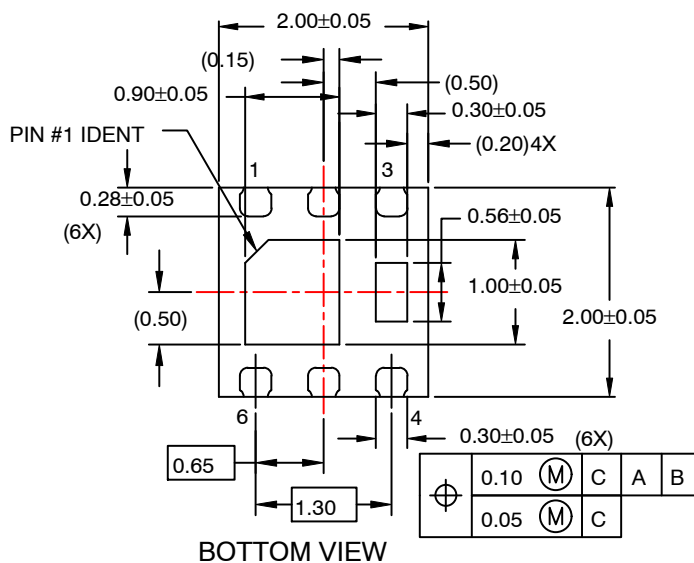
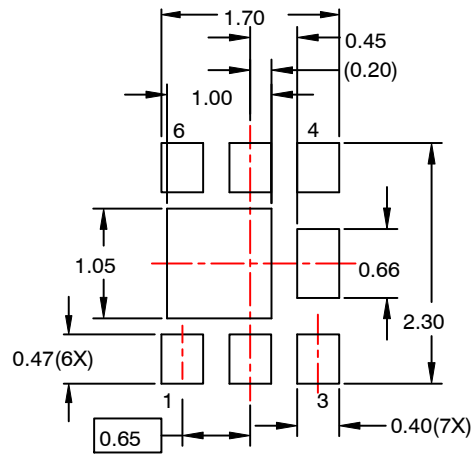
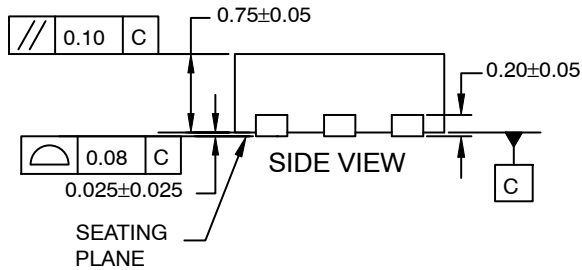
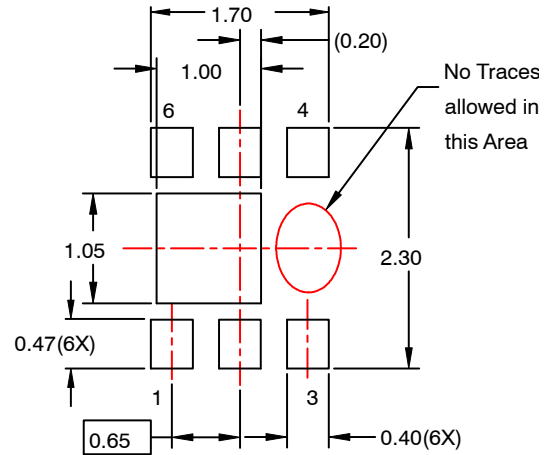
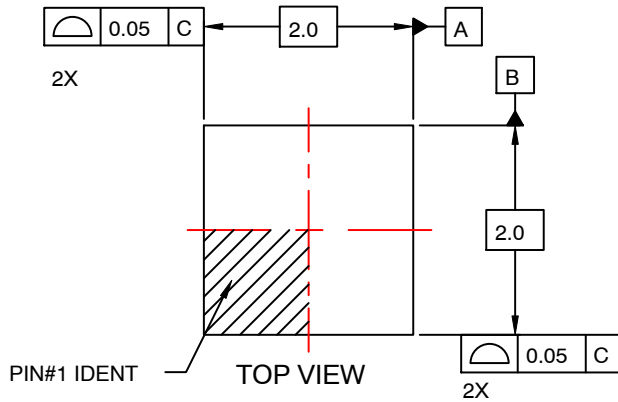
PACKAGE DIMENSIONS

ON Semiconductor®



WDFN6 2x2, 0.65P
CASE 511CZ
ISSUE O

DATE 31 JUL 2016



NOTES:

- A. PACKAGE DOES NOT FULLY CONFORM TO JEDEC MO-229 REGISTRATION
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.
- D. LAND PATTERN RECOMMENDATION IS EXISTING INDUSTRY LAND PATTERN.

DOCUMENT NUMBER:	98AON13614G	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	WDFN6 2X2, 0.65P	PAGE 1 OF 1

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales

